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Journal

ACS Nano, 18(7)

ISSN

1936-0851

Authors

Wang, Shu

Higashitarumizu, Naoki

Sari, Bengisu

et al.

Publication Date

2024-02-09

DOI

10.1021/acsnano.3c12927

Peer reviewed

Quantitative mid-infrared photoluminescence characterization of black phosphorus-arsenic alloys

Shu Wang^{1,2,3}, Naoki Higashitarumizu^{2,3,4}, Bengisu Sari^{1,2,5}, Mary C. Scott^{1,2,5}, Ali Javey^{2,3,4,*}

1. Department of Materials Science and Engineering, University of California, Berkeley, CA 94720, USA.

2. Materials Sciences Division, Lawrence Berkeley National Laboratory, Berkeley, CA 94720, USA.

3. Berkeley Sensor & Actuator Center, University of California, Berkeley, CA 94720, USA.

4. Electrical Engineering and Computer Sciences, University of California, Berkeley, CA 94720, USA.

5. The National Center for Electron Microscopy, Molecular Foundry, Berkeley, CA 94720, USA.

* Corresponding author email: ajavey@berkeley.edu

Abstract:

Black phosphorus (bP) is a promising material for mid-infrared (mid-IR) optoelectronic applications, exhibiting high performance light emission and detection. Alloying bP with arsenic extends its operation towards longer wavelengths from 3.7 μm (bP) to 5 μm (bP₃As₇), which is of great practical interest. Quantitative optical characterizations are performed to establish black phosphorus-arsenic (bPAs) alloys optoelectronic quality. Anisotropic optical constants (refractive index, extinction coefficient, and absorption coefficient) of bPAs alloys from near-infrared to mid-IR (0.2-0.9 eV) are extracted with reflection measurements, which helps optical device design. Quantitative photoluminescence (PL) of bPAs alloys with different As concentrations are measured from room temperature to 77 K. PL quantum yield measurements reveal two orders of magnitude decrease in radiative efficiency with increasing As concentration. Optical cavity is designed for bP₃As₇, which allows for to up to an order of magnitude enhancement in the quantum yield due to the Purcell effect. Our comprehensive optical characterization provides the foundation for high performance mid-IR optical device design using bPAs alloys.

Keywords: Phosphorus-arsenic alloys, photoluminescence quantum yield, Mid-IR, anisotropic, optical constant, positive bandgap temperature coefficient, optical cavity

* Corresponding.

Mid-infrared (mid-IR) optoelectronics have been of considerable importance for applications in sensing, imaging, and communication. However, mid-IR light sources suffer from high power consumption (*e.g.*, quantum and interband cascade lasers) and/or low radiative efficiency (*e.g.*, light emitting diodes). This performance limitation is partly due to the enhanced Auger recombination rate as the semiconductor bandgap is reduced to mid-IR.¹ Black phosphorus (bP), with a bulk direct energy band gap of 0.33 eV (3.7 μm), has shown great promise for high-performance mid-IR photodetectors and emitters.² Notably, as compared to conventional III-V and II-VI semiconductors with similar bandgap, bP exhibits a lower Auger recombination rate³ due to its more symmetric electron/hole effective mass.^{1,4,5} To further the applications of black phosphorus towards longer wavelengths, various techniques have been demonstrated, including applying compressive strain,^{6,7} tuning with electric field,⁸ applying pressure,⁹ and alloying with other group V elements such as arsenic.¹⁰⁻¹³ Alloying is promising as it can be directly incorporated into existing device designs.

In the past few years, various studies have demonstrated mid-IR photodetectors (phototransistor and photodiode, with high responsivity) with black phosphorus arsenic (bPAs) alloys,¹⁰⁻¹³ while electroluminescence of bPAs heterostructure¹⁴ and simulated emission of bPAs in cavity in 3.4 – 4.7 μm ¹⁵ have been reported recently. Despite considerable research highlighting bPAs mid-IR optoelectronic device potential,^{11,12,14,16} detailed quantitative optical characterization as a function of As concentration is still lacking. Such data is needed for optimal design of bPAs optoelectronic devices while projecting their performance limits.

In this paper, we perform comprehensive bPAs alloys photoemission and optical absorption measurements using customized Fourier-transform infrared spectroscopy (FTIR) for As

concentration from 0% to 70%. Refractive index (n) and extinction coefficient (k) of bPAs alloys from 0.2 eV to 0.9 eV are extracted using thickness dependent reflection measurement. Anisotropic absorption of bPAs is demonstrated with a polarized refraction study. Photoluminescence quantum yields (PLQY) for bPAs alloys are measured. Using the optical constants measured in this work, optimal optical cavities are designed with increased Purcell factor, demonstrating an order of magnitude enhancement in PLQY. Temperature dependent PL from 77 K to room temperature for bPAs alloys are studied. Our results can be used to design high performance mid-IR optoelectronic devices in 3 μm to 5 μm with bPAs alloys.

BPA alloy is mechanically exfoliated in a nitrogen glove box and measured in a vacuum chamber, with HgCdTe (MCT) detector in an FTIR set up with lock-in detection (see method).^{6,17,18} BPA alloys with thicknesses ranging from 20 nm to 1 μm are measured. As shown in **Figure 1**, bPA PL bandgap changes from 0.33 eV for bP to 0.28 eV for bP₃As₇, which corresponds to wavelength change from 3.7 μm to 4.4 μm . No significant difference in the PL spectrum is observed for the measured thickness range (see **Figure S4**), as the explored thickness is large enough to minimize quantum confinement effects. Choice of relatively thick samples (>20 nm, where blue-shift of bandgap due to quantum effect is negligible) is in consideration of its application in mid-IR, where the performance of both light emission and detection devices still has much to improve. The upper thickness limit of samples used in this study (1 μm) is determined by the measured absorption depth, as will be detailed below. No significant PL spectrum change is observed in the incident light power range, except a small increase of spectrum full-width-at-half-maximum (FWHM) with increased power due to local heating (**Figure S4**). A small absorption dip is observed for bP₃As₇ PL spectrum at 0.29 eV (also evident bP₅As₅), due to the atmospheric carbon dioxide (~ 500 ppm) absorption, indicating high sensitivity for bPAs in application of environmental sensing.^{6,19}

The composition and material quality used in this study is characterized by energy dispersive X-ray spectroscopy (EDS), Raman spectrum, and transmission electron microscope (TEM). Scanning electron microscope EDS characterization reveals the alloy compositions of each sample (bP, bP₉₅As₅, bP₅As₅ and bP₃As₇, see **Figure 2** and **Figure S1**). The polarization resolved Raman spectra for different bPAs alloys are measured, as shown in **Figure 2**. Feature Raman peak positions for bP (362 cm⁻¹, 440 cm⁻¹, and 467 cm⁻¹) and As (between 210 cm⁻¹ to 260 cm⁻¹), along with the gradual shift and broadening of peak position due to alloying are evident, which shows the compositional difference for the samples used in this paper.^{20,21} Clear evidence of polarization dependence can be observed for the material from the Raman spectra, especially for bP and 5 at% As alloy (more than 1 order intensity difference for A_g¹ mode, see **Figure S2**). High-resolution transmission electron microscopy (HRTEM) images for bP₃As₇ and bP₉₅As₅ show the crystal quality of samples used (**Figure 3**). Selected area electron diffraction (SAED) patterns of bP₃As₇ and bP₉₅As₅ along z axis demonstrate the crystallinity of the samples, with the extracted lattice constants (a = 3.3 Å, c = 4.4 Å for bP₉₅As₅, a = 3.57 Å, c = 4.2 Å for bP₃As₇) and the diffraction patterns match that of orthorhombic bPAs alloys (**Figure 3, Figure S5**).^{22,23} The lattice constant for bP₉₅As₅ is similar to that of bP. Interestingly for bP₃As₇, the armchair direction lattice constant is larger than reported value for bP and black arsenic (bAs), zigzag direction lattice constant is smaller than bP and bAs, probably due to the atom size difference of P and As.^{24,25}

Besides bandgap and material quality, optical constants (refractive index, n, and extinction coefficient, k) of a material are important for optical device design. Here, the refraction spectra of bPAs alloys are measured as a function of material thickness. Exfoliated bPAs alloys with thicknesses from 50 to 500 nm are used for each composition (10 – 20 evenly spaced thicknesses). With thin film transfer matrix theory, (n, k) values can be extracted from the measured refraction

spectra.^{26,27} **Figure 4** shows the measured refraction spectra for three compositions of bPAs alloys on Au substrate as a function of sample thickness. The clear effect of thin-film interference due to different n , k , and thickness values of the layers is observed. Light absorption on X direction is significantly higher than on Y direction, as evidenced by the reduced reflection. The detailed anisotropic features of bPAs alloys are demonstrated in **Figure 5**, with measured reflection spectra of individual exfoliated flakes using polarized light ranging from 0 degree to 170 degrees. From the measured reflection, X direction (armchair) is denoted as the direction with maximum absorption of light, while Y direction (zigzag) is denoted as the direction with minimum absorption of light (thus maximum reflection), which is how X and Y direction in **Figure 4** is determined. Applying thin-film transfer matrix method (details in method section),²⁶ fitted (n , k) values from 0.2 eV to 0.9 eV from data measured in **Figure 4** are shown in **Figure 6**. The absorption coefficient, α , is calculated from the extinction coefficient and wavelength ($\alpha = \frac{4\pi k}{\lambda}$, where λ is wavelength). Absorption edges, which correspond to energy band edges, for the alloys can be observed in X direction k (or α) values. The energy bandgaps extracted from fitted (n , k) values are 0.32 eV for bP, 0.31 eV for bP₉₅As₅, 0.26 eV for bP₅As₅, 0.255 eV for bP₃As₇ (**Figure 7**), which is consistent with extracted bandgaps from PL measurements. The absorption coefficient is $1-2 \times 10^4 \text{ cm}^{-1}$ for 0.4 - 0.9 eV in the X direction, which indicates the absorption depth is around 500 nm to 1 μm .

Photoluminescence quantum yield is a key merit for characterizing the radiative to non-radiative recombination rate of an emission material.²⁸ We measured the PLQY for the bPAs alloys as shown in **Figure 8**.⁶ Laser polarization is aligned to the X direction (maximum absorption) with ± 30 degrees accuracy, as in the crystal orientation where light absorption is weak, the PL signal

is weak and measurement error is large. With 5 at% As incorporation, PLQY is still comparable to bP (decrease ~ 3 times); when the As concentration increases to 70%, 2 orders of magnitude decrease of PLQY is observed. A general trend of decreasing PLQY with increasing generation rate is observed, which could be the result of stronger Auger recombination at higher carrier concentrations. A decrease of PLQY with decreasing thickness is observed for bP₉₅As₅, which can be attributed to a higher surface to volume ratio and thus an increasing effect of non-radiative surface recombination.

Stronger Auger recombination due to smaller bandgap contributes to the lowering of PLQY when As concentration increases in bPAs alloys. The ratio of Auger coefficient to radiative coefficient changes exponentially with bandgap: $\frac{\tau_{Auger}}{\tau_{rad}} \propto \exp\left[\frac{m_c}{m_c+m_h} \cdot \frac{E_g}{k_B T}\right]$, where τ_{Auger} is Auger recombination lifetime, τ_{rad} is radiative recombination lifetime, m_c and m_h are effective masses for electron and hole, E_g is bandgap, $k_B T$ is thermal energy.^{1,6} Besides stronger Auger recombination for bPAs alloys with high As concentration, the crystal quality of the material contributes to the lowering of PLQY. Note that typical efficiency for 4 μm light emitting diode is 10^{-3} (for epitaxial quantum wells or HgTe colloidal quantum dot).²⁹⁻³¹ For practical applications of bPAs alloys for light emission, designs to enhance radiative recombination are needed, including low temperature operation or incorporation of an optical cavity as reported below.

Nonradiative recombinations are typically suppressed at low temperatures, where phonon assisted processes are suppressed due to lower available thermal energies. The energy bandgap of a semiconductor commonly increases with decreasing temperature,³² while some materials including bP show positive bandgap temperature coefficient.³³⁻³⁵ To study the effect of temperature on bPAs alloys luminescence properties, we measure temperature dependent PL for

bP, bP₉₅As₅, bP₅As₅, and bP₃As₇. All samples are exfoliated in a nitrogen environment, before transferring to a vacuum chamber and cool down to 77 K. Subsequent PL spectra are measured while the vacuum chamber warms up towards room temperature. PL peak position at 77 K changes from 0.31 eV for bP to 0.25 eV for bP₃As₇ (**Figure 9, Figure S6**). Contrary to that observed at room temperature, the lower energy side of the spectrum is broader (**Figure S6, Figure 1**), which may be attributed to band tailing. PL spectra as a function of temperature are shown in **Figure 9**, with extracted peak positions and spectra full width at half maximum (FWHM) (**Figure 10**). Positive temperature coefficient is observed for all compositions. Small decreasing trend for the bandgap temperature coefficient is observed when the As concentration increases ($1.6 \times 10^{-4} \text{ eV/K}$ for bP, to $1.2 \times 10^{-4} \text{ eV/K}$ for bP₃As₇). The PL spectra are sharper at lower temperatures (FWHM changes from 40 meV to 65 meV). As shown in **Figure 10**, a clear enhancement of radiative recombination at 77 K is observed. The integrated counts from the PL spectra (which is proportional to radiative quantum efficiency) show gradual increase when temperature decreases, reaching 2x enhancement at 77 K.

Spontaneous radiative emission rate of a material can be influenced by its dielectric environment. The Purcell factor quantitatively describes the effect of cavity on the radiative emission rate. With designed cavity, the Purcell factor changes by orders of magnitude, significantly extending the application ability of an optical material.^{15,17,36} Due to its interlayer van der Waals bonding nature, bPAs alloys can be readily incorporated into designed optical cavities without sacrificing its radiative emission rate.^{17,18} Here, we fabricate an optical cavity with increased Purcell factor (~20) compared to the Si wafer substrate used for the rest of the paper. As illustrated in **Figure 11**, the cavity for bP₃As₇ consists of a bottom Au reflector and top ITO half-reflector, with Al₂O₃ and h-BN as spacer. The measured PL spectrum of the bP₃As₇ inside the cavity is consistent with that

measured on Si wafers. Small blue shift and broadening of PL is observed, which results from local heating due to enhanced (2x) absorption and high pump power. The PLQY with cavity is significantly enhanced, reaching 0.5%, which is comparable to bP of similar thickness. The effect can also be understood by constructive interference of PL from bPAs. The extreme circumstance of this cavity enhancement will be lasing,^{15,36} which requires more dedicated device fabrication techniques and thus beyond the scope of this work. Nevertheless, the demonstration of the enhanced luminescence yield of bPAs alloy shows its promise for high performance mid-IR emission device, especially when considering layered materials like bPAs alloy do not have as much constraint for lattice matching as traditional III-V and II-VI semiconductors.

To summarize, we report optical and optoelectronic properties for bPAs alloys for mid-IR light emission and detection applications. BPAs alloys room temperature luminescence wavelength extend to 4.4 μm with bP₃As₇. A significant decrease in radiative emission efficiency is observed for high As concentration bPAs alloys, which can be compromised by incorporating an optical cavity. Anisotropic optical constants measured for bPAs alloys from 0.2 eV to 0.9 eV provide the building block for optical device design. Positive temperature dependence of optical bandgap indicates negative pressure coefficient and/or non-traditional electron-phonon coupling in this layered alloy system. Further development of practical mid-IR optoelectronics with bPAs alloys will benefit from cavity (for increased radiative recombination), surface treatment or packaging (for long operation lifetime), as well as large-scale high-quality synthesis of bPAs material.

Method

Materials

Black phosphorus – arsenic alloys are purchased from hQ graphene (chemical vapor transport synthesis with Tin as catalyst), stored in a nitrogen box, and used as received. Samples are exfoliated with Scotch tape, transferred to PDMS, and finally transferred to target substrates. For reflection measurements, substrates are Au, which is 5 nm Ti + 80 nm Au evaporated on clean Si wafers. For cavity, the substrate is evaporated 100 nm Au + sputtered 180 nm Al₂O₃ on clean Si wafer. For all other PL measurements, substrate is Si wafer with 50 nm SiO₂.

Material characterization

Energy dispersive X-ray spectroscopy is measured with FEI Quanta scanning electron microscopy at The California Institute for Quantitative Biosciences at UC Berkeley. Samples used in this study show small variation (3%), especially for bP₅As₅ and bP₃As₇ alloys (**Figure S1**). Along with the 1% error inherent in EDS analysis, the composition should be interpreted with error in mind.

The Raman spectrum is measured with a commercial Raman (Horiba Labram HR evolution) with 473 nm laser focused on samples by 100X objective at UC Berkeley.

Transmission electron microscope characterization (high-resolution transmission electron microscopy and selected area electron diffraction) is measured with a FEI Titan 60-300 microscope with acceleration voltage 300 kV at the National Center for Electron Microscopy at Lawrence Berkeley National Laboratory. Samples for TEM are prepared in a nitrogen glove box. First exfoliate source material with Scotch tape, then transfer flakes from Scotch tape to PDMS, then transfer flakes from PDMS to clean Si wafer (with 50 nm oxide), then add 5 microliter ethanol alcohol on the TEM grid (G100HS, Copper, Tedpella) placed near the target flake on the Si wafer, then finally anneal at 90 degree C and check with optical microscope.

FTIR PL measurement

Photoluminescence measurement with customized set up using FTIR + lock-in amplifier has been reported previously.^{6,17,18} Samples are exfoliated in a nitrogen glove box and quickly transferred to the vacuum chamber. Sample inside a vacuum chamber (CaF₂ window, < 1e-5 torr) is excited with modulated 638 nm laser, with emission collected by an FTIR (Thermo Scientific, Nicolet is50) with a 15x reflective objective lens, where PL signal (not thermal background) is extracted using lock-in detection technique modulated at 5k Hz. Polarization is aligned with rotating the sample perpendicular to the laser until maximum PL intensity. For quantitative PL study, set up collection efficiency is calibrated using 4 μm QCL laser with Spectralon placed at the sample position, while thin film absorption / emission properties are simulated with finite-difference time-domain method (Ansys Lumerical).

FTIR polarized reflection measurement

FTIR left microscope is used for micro-reflection measurement. Built-in IR source (1000 K thermal source) is directed towards a 32x reflective objective focused on either the sample or the Au reflection reference. CaF₂ holographic wire grid polarizer (Thorlabs) is used for creating a polarized light source from the IR source. BPAs alloy samples are measured in air within 4 hours of exfoliation to minimize the effect of ambient conditions on their surfaces.

Thin film transfer matrix method

Equation for analyzing multilayer systems adopted from reference, which considers multi-reflection and light interference.²⁶ Normal incidence on perfect thin-film stack is assumed. The method is briefed as follows:

Amplitude reflection r of semi-infinite film stack is:

$$r = \frac{n_m E_m - H_m}{n_m E_m + H_m}$$

where E_m and H_m are electric vector and magnetic vector, n_m is the refractive index of layer m :

$$\begin{pmatrix} E_m \\ H_m \end{pmatrix} = M \begin{pmatrix} 1 \\ n_s \end{pmatrix}$$

M is a product matrix:

$$M = M_L M_{L-1} \dots M_1$$

$$M_j = \begin{pmatrix} \cos\delta_j & \frac{i}{n_j} \sin\delta_j \\ in_j \sin\delta_j & \cos\delta_j \end{pmatrix}$$

with $\delta_j = \frac{2\pi}{\lambda} (n_j d_j)$, λ is light wavelength, d_j is thickness of layer j .

The intensity reflectance for thin film stack of air, bPAs and Au is:

$$R = |r|^2 = \left| \frac{\cos\delta_j - \cos\delta_j \cdot n_{Au} + i \frac{n_{Au}}{\eta_{bPAS}} \sin\delta_j - i \eta_{bPAS} \sin\delta_j}{\cos\delta_j + \cos\delta_j \cdot n_{Au} + i \frac{n_{Au}}{\eta_{bPAS}} \sin\delta_j + i \eta_{bPAS} \sin\delta_j} \right|^2$$

where $\delta_j = \frac{2\pi}{\lambda} (\eta_{bPAS} d_{bPAS})$, η_{bPAS} is complex refractive index of bPAs, d_{bPAS} is thickness of bPAs, n_{Au} is complex refractive index of Au.³⁷

The measured data is fitted with the R equation above with least-square method. Complete reconstruction of experimental data using fitted (n, k) values can be found in supporting information.

Cavity fabrication

Si wafer evaporated with 100 nm Au and sputtered with 180 nm Al₂O₃ is used for exfoliation substrate of bPAs. Thickness of bPAs is measured with atomic force microscope (AFM, Dimension Icon with ScanAsyst from Bruker). Separately, h-BN (purchased from hQ graphene) is exfoliated with Scotch tape and transferred to Si wafers using PDMS. ITO is sputtered on top of h-BN, where the thickness of h-BN is measured with AFM. Poly(methyl methacrylate) (PMMA) dry transfer is used for transferring h-BN-ITO to bPAs. In brief, PMMA is transferred on top of h-BN-ITO, annealed at 180 °C for 90 seconds, picked up and transferred on top of target bPAs, annealed at 180 °C for 3 minutes, and finally dissolved in dichloromethane (DCM).

Supporting information.

Figure S1. BPAs composition from SEM-EDS. Figure S2. Polarized Raman spectra for bPAs (alloys). Figure S3. Reconstructed anisotropic reflection of bPAs alloys with different thicknesses on Au from fitted (n,k) values. Figure S4. Thickness and power dependence of photoluminescence (PL) spectra for bPAs alloys. Figure S5. TEM crystal structure analysis of bPAs alloys. Figure S6. Low temperature PL spectra for bPAs (alloys). This material is available free of charge via the Internet at <http://pubs.acs.org>.

Acknowledgement

This work was supported by the U.S. Department of Energy, Office of Science, Office of Basic Energy Sciences, Materials Sciences and Engineering Division under contract No.DE-AC02-05-CH11231 (EMAT program KC1201).

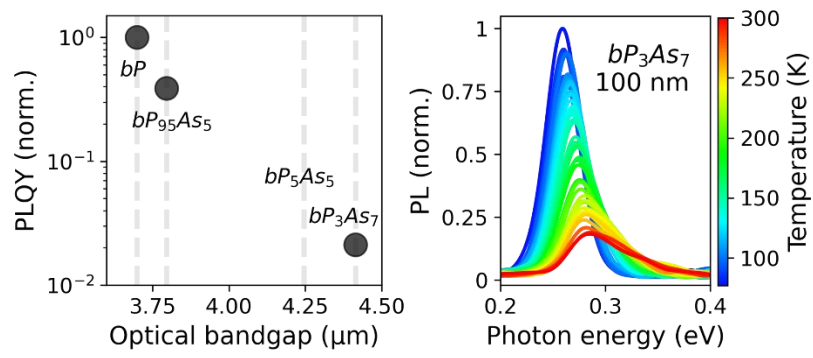
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Figures and captions



TOC figure

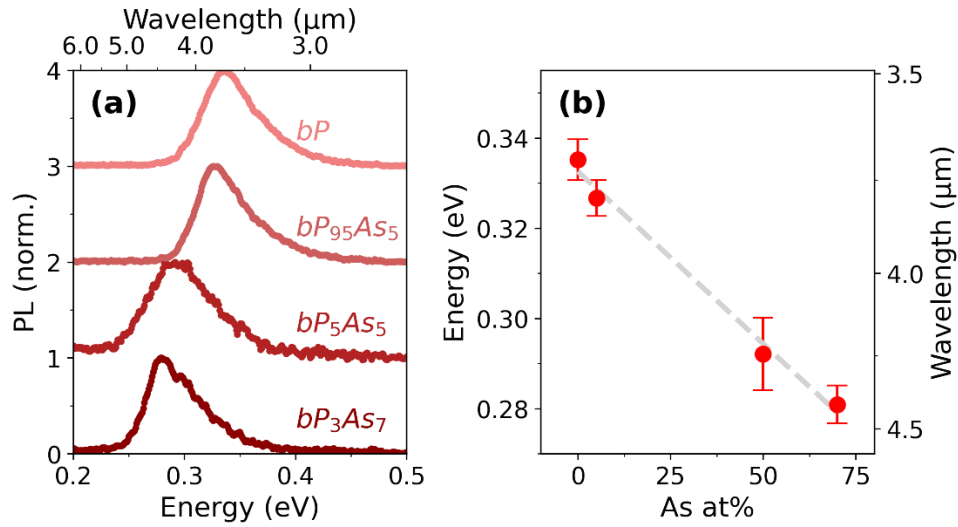


Figure 1. Photoluminescence of bPAs alloys. (a) Normalized photoluminescence spectra of bP, bP₉₅As₅, bP₅As₅, and bP₃As₇ at room temperature. (b) Optical bandgap extracted from photoluminescence spectra in (a). Linear fit is shown. Error bars show standard deviations calculated from extracted peak positions of multiple (~ 20) measurements at each alloy composition.

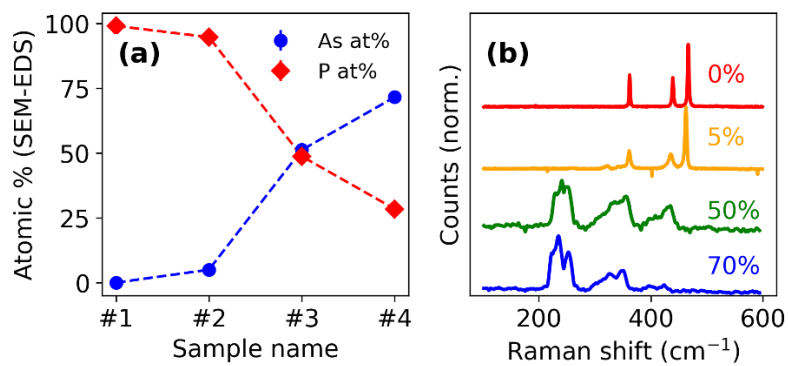


Figure 2. Material characterization (Raman and EDS) of samples studied in this paper. **(a)** Energy-dispersive X ray spectroscopy of bPAs alloys showing their atomic composition. Sample numbers 1,2,3,4 correspond to bP, bP₉₅As₅, bP₅As₅, and bP₃As₇ used in this paper. **(b)** Unpolarized Raman spectra for bP, bP₉₅As₅, bP₅As₅, and bP₃As₇.

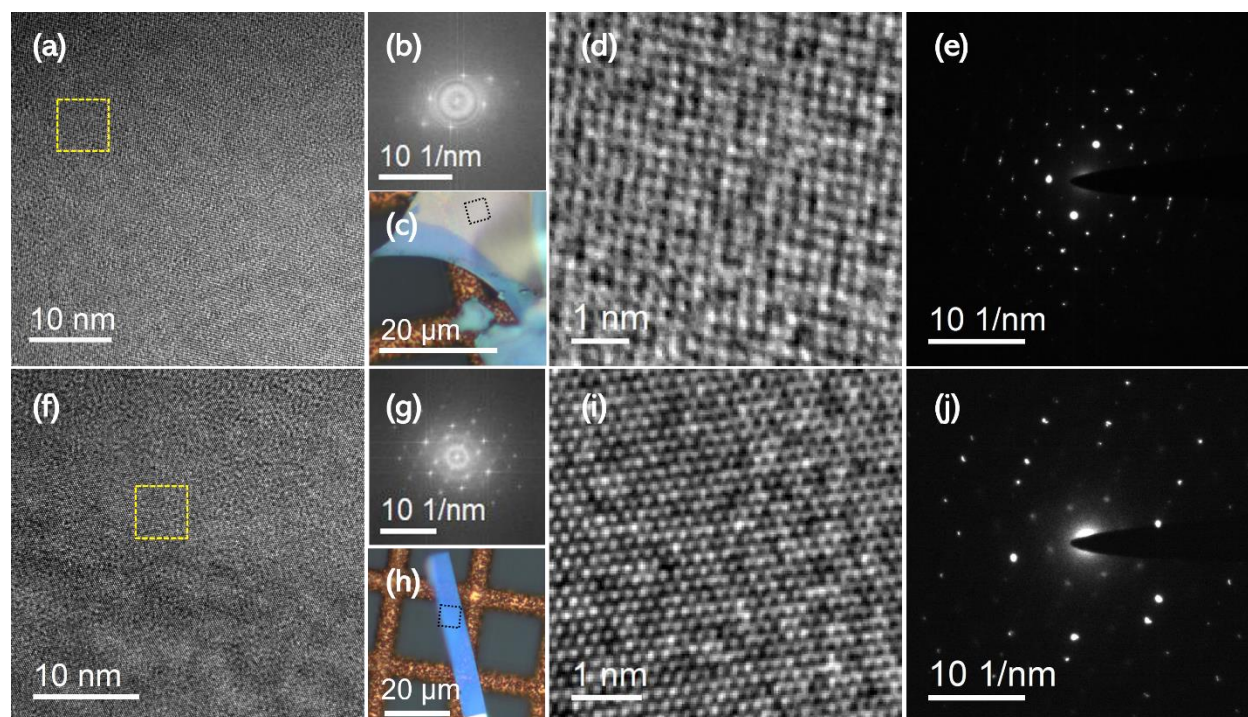


Figure 3. TEM characterization bPAs alloys. **(a-e)** bP_3As_7 **(f-j)** $\text{bP}_{95}\text{As}_5$ **(a)** HRTEM image of bP_3As_7 alloy. **(b)** Fast Fourier transform of image (a) **(c)** Optical microscope image of the sample used for TEM imaging in (a-e), where the imaged area is marked in dashed black square. **(d)** magnified HRTEM image of sample area marked in yellow dashed square in (a) **(e)** parallel beam diffraction pattern of sample shown in (c) with camera length 160 mm and 300 kV. **(f)** HRTEM image of $\text{bP}_{95}\text{As}_5$ alloy. **(g)** Fast Fourier transform of image (f) **(h)** Optical microscope image of the sample used for TEM imaging in (f-j), where the imaged area is marked in dashed black square. **(i)** magnified HRTEM image of sample area marked in yellow dashed square in (f) **(j)** parallel beam diffraction pattern of sample shown in (h) with camera length 160 mm and 300 kV.

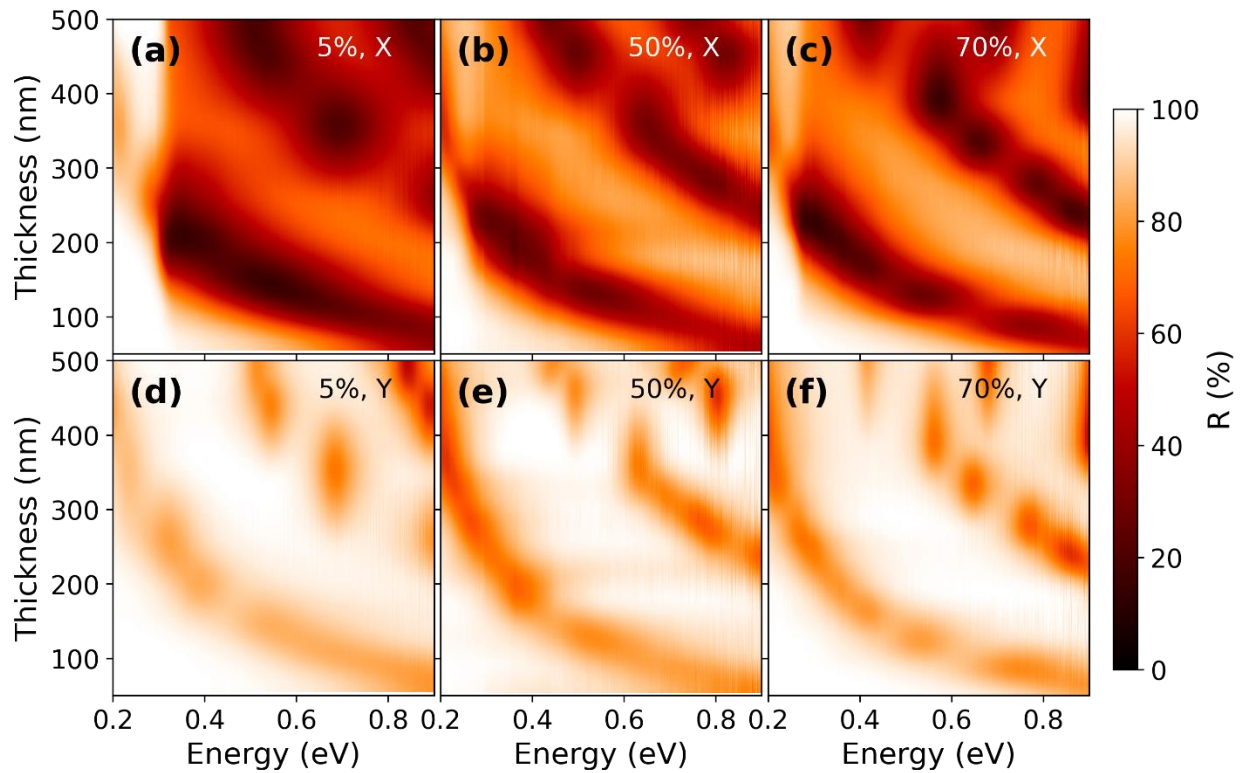


Figure 4. Anisotropic reflection of bPAs alloys with different thicknesses on gold. **(a, b, c)** Armchair (X) direction reflection of $\text{bP}_{95}\text{As}_5$, bP_5As_5 , and bP_3As_7 on gold. **(d, e, f)** Zigzag (Y) direction reflection of $\text{bP}_{95}\text{As}_5$, bP_5As_5 , and bP_3As_7 on gold.

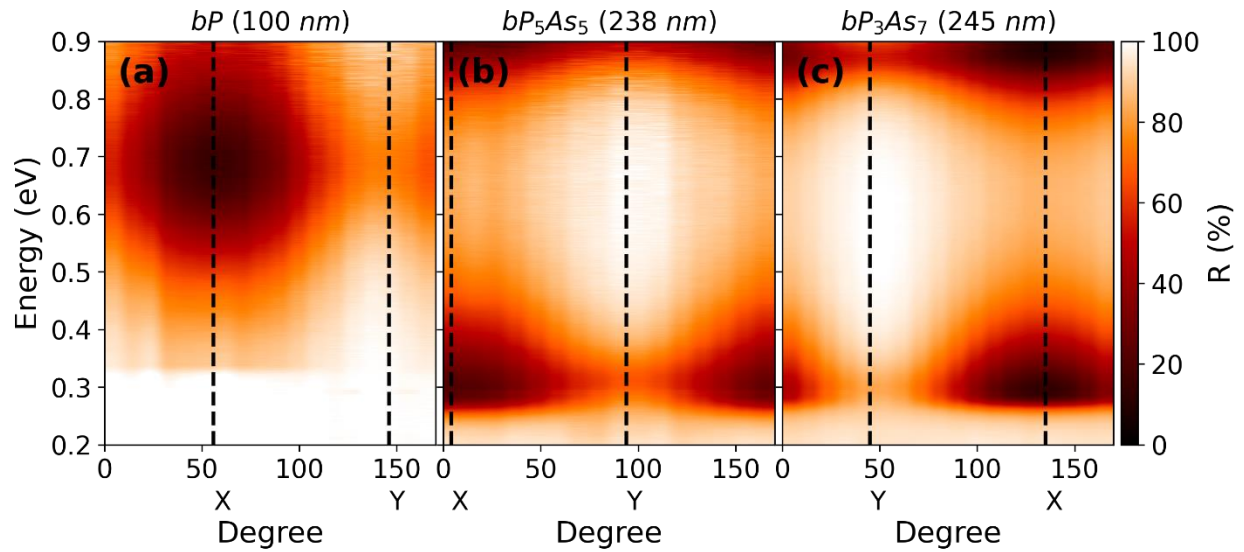


Figure 5. Anisotropic reflection of bPAs (alloy) on gold. **(a)** bP reflection on gold, with light polarization from 0 to 170 degree. **(b)** bP₅As₅ reflection on gold, with light polarization from 0 to 170 degree. **(c)** bP₃As₇ reflection on gold, with light polarization from 0 to 170 degrees. Armchair (X) and Zigzag (Y) directions determined from minimum and maximum reflection, as shown in each subplot, and used for determining X and Y directions for Figure 4.

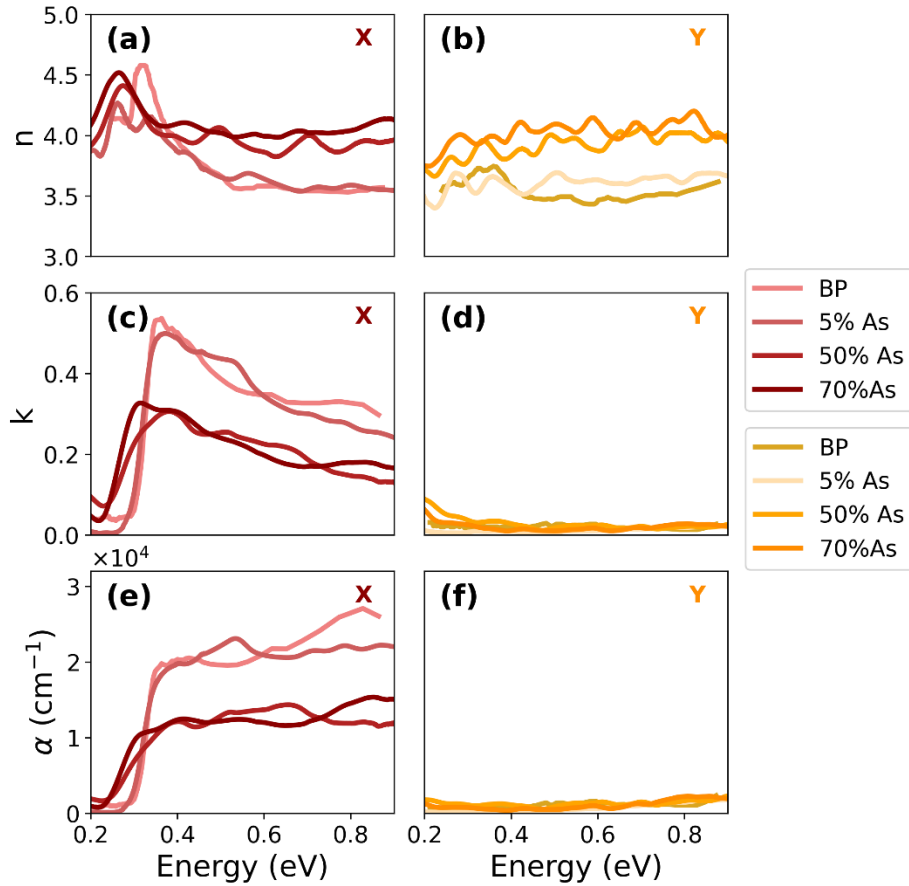


Figure 6. Optical constants of bPAs alloys. Data from fitting polarized reflection measurements of bPAs alloys with different thicknesses shown in Figure 4. Fitting adopts transfer matrix method. **(a, c, e)** Armchair (X) direction optical constants (n , k , α) for bP, bP₉₅As₅, bP₅As₅, and bP₃As₇. **(b, d, f)** Zigzag (Y) direction optical constants (n , k , α) for bP, bP₉₅As₅, bP₅As₅, and bP₃As₇. BP data adopted from Nat. Photonics 2018.²⁷

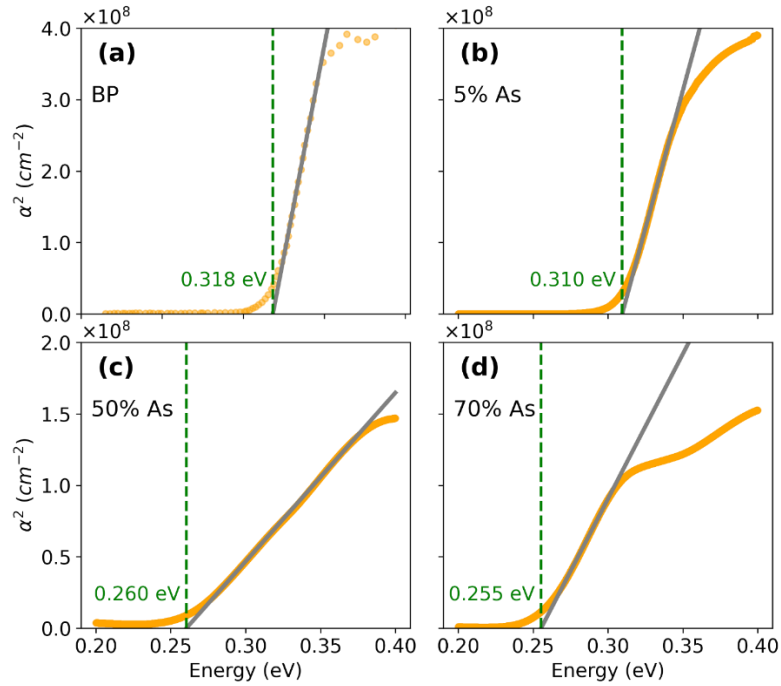


Figure 7. BPAs (alloy) bandgap estimation from extracted optical constant. **(a)** Bandgap estimation for BP. **(b)** Bandgap estimation for $\text{bP}_{95}\text{As}_5$. **(c)** Bandgap estimation for bP_5As_5 . **(d)** bandgap estimation for bP_3As_7 . BP data adopted from Nat. Photonics 2018.²⁷

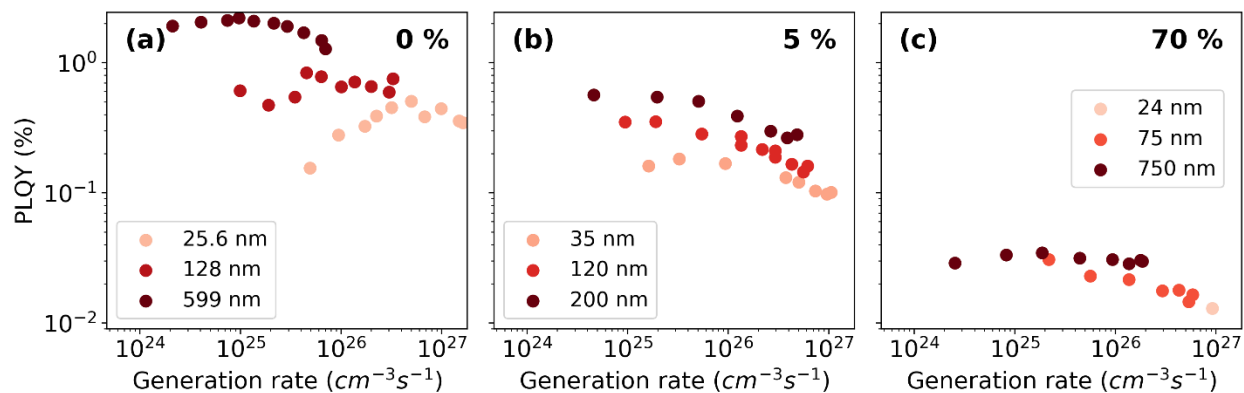


Figure 8. Photoluminescence quantum yield of bPAs alloys. **(a)** PLQY of bP (data adapted from Nat. Nano. 2023).¹⁷ Different colors represent different thicknesses, where light red is 25.6 nm, red is 128 nm, and dark red is 599 nm. **(b)** PLQY of bP₉₅As₅. The colors of the scatter plot represent different thicknesses, where light red is 35 nm, red is 120 nm, and dark red is 200 nm. **(c)** PLQY of bP₃As₇. Specimens of different thicknesses are represented with color, where light red is 24 nm, red is 75 nm, and dark red is 750 nm.

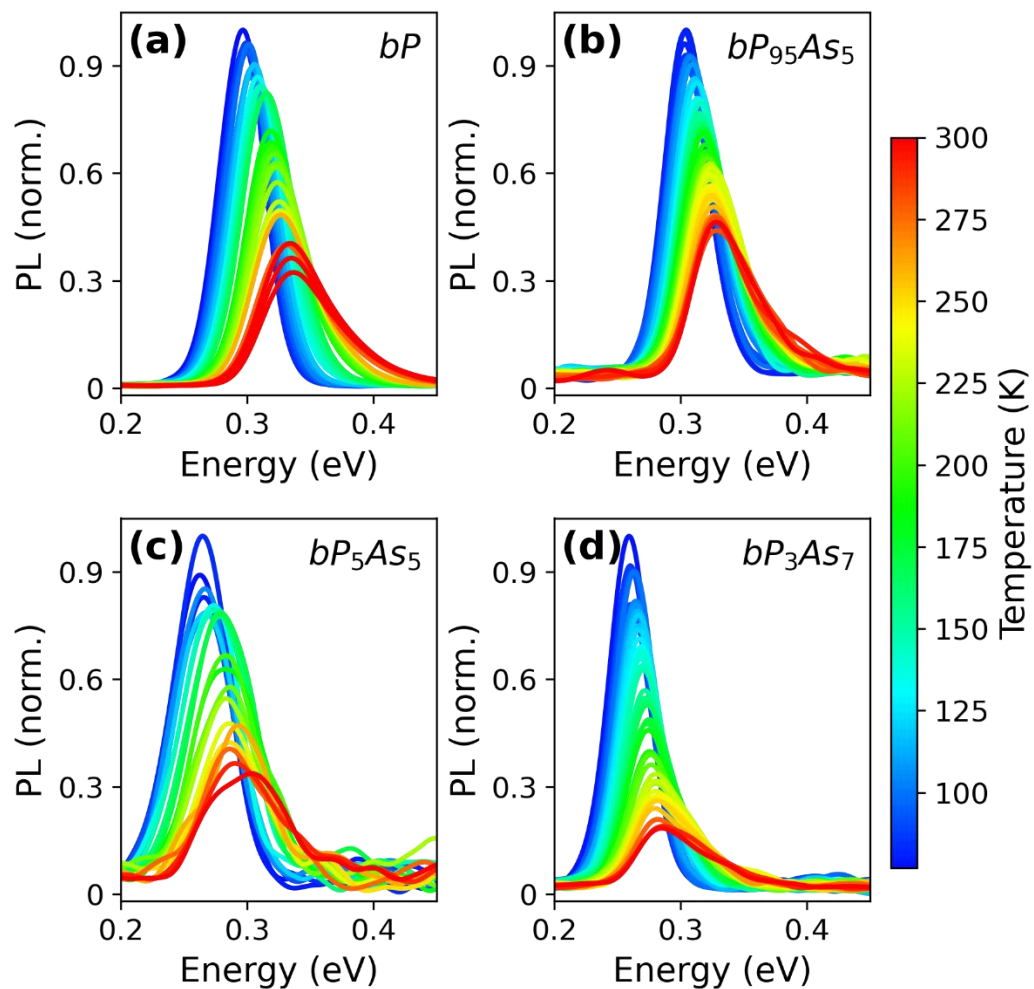


Figure 9. Temperature dependent photoluminescence spectra of bPAs alloys. **(a-d)** PL spectra from 77 K to room temperature for bP, $bP_{95}As_5$, bP_5As_5 , and bP_3As_7 . Thicknesses are 500 nm for bP, 94.6 nm for $bP_{95}As_5$, 250 nm for bP_5As_5 , and 100 nm for bP_3As_7 .

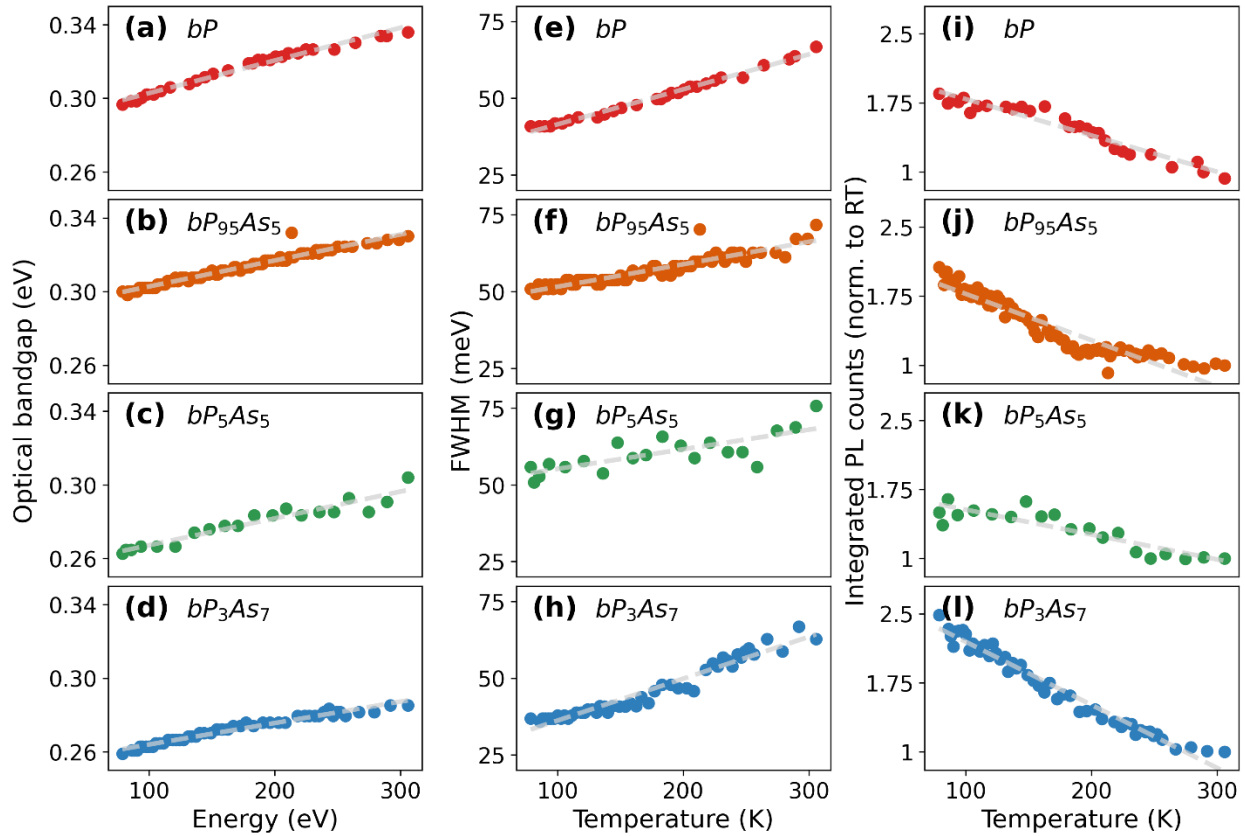


Figure 10. Temperature dependent photoluminescence data of bPAs alloys. **(a-d)** Optical bandgap extracted from PL spectra in Figure 9 from 77 K to room temperature for bP , $bP_{95}As_5$, bP_5As_5 , and bP_3As_7 . **(e-h)** Full width at half maximum (FWHM) extracted from PL spectra in Figure 9 from 77 K to room temperature for bP , $bP_{95}As_5$, bP_5As_5 , and bP_3As_7 . **(i-l)** Integrated counts from PL spectra in Figure 9 from 77 K to room temperature for bP , $bP_{95}As_5$, bP_5As_5 , and bP_3As_7 . Counts normalized to each room temperature counts. Linear fitted is shown for each subfigure.

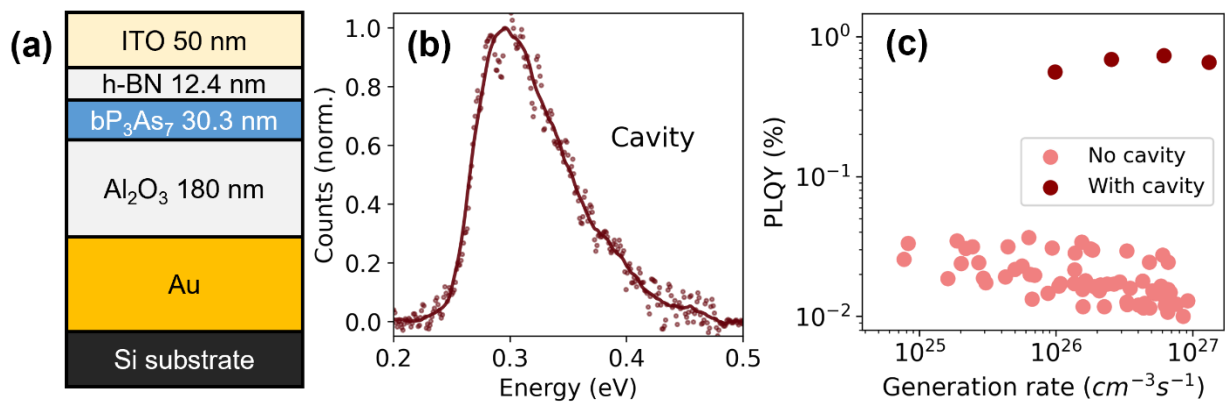


Figure 11. Optical cavity design for high quantum yield emitter with bP₃As₇. **(a)** Cavity structure. **(b)** Normalized photoluminescence spectrum of bP₃As₇ in the cavity. Note the spectrum is slightly blue shift due to local heating. **(c)** Estimated PLQY for the cavity (30.3 nm), as compared to samples directly exfoliated on Si wafers (multiple samples with thicknesses 20 nm – 1 μm).